Inverter

HITACHI

ADE-205-303B (Z) 3rd. Edition April 2001

Description

The HD74HCT1G04 is high speed CMOS inverter using silicon gate CMOS process. With CMOS low power dissipation, it provides high speed equivalent to LS-TTL series. The internal circuit of three stages construction with buffer provides wide noise margin and stable output.

Features

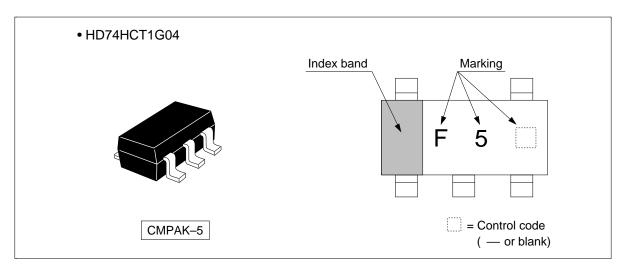
- The basic gate function is lined up as hitachi uni logic series.
- Supplied on emboss taping for high speed automatic mounting.
- TTL compatible input level.

Supply voltage range: 4.5 to 5.5 V

Operating temperature range: -40 to +85°C

• $|I_{OH}| = I_{OL} = 2 \text{ mA (min)}$

Outline and Article Indication



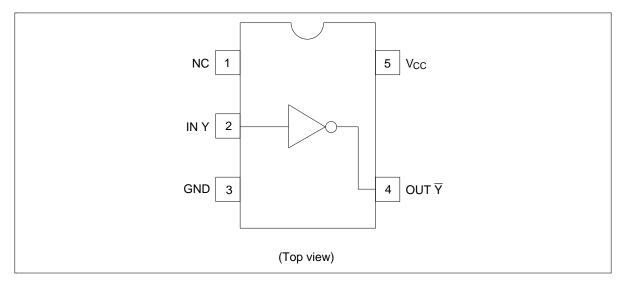


Function Table

Input A	Output Y				
Н	L				
L	Н				

H : High level L : Low level

Pin Arrangement



Absolute Maximum Ratings

Item	Symbol	Ratings	Unit	Test Conditions
Supply voltage range	V _{cc}	-0.5 to 7.0	V	
Input voltage range *1	V _I	-0.5 to V_{cc} + 0.5	V	
Output voltage range *1, 2	Vo	-0.5 to V_{cc} + 0.5	V	Output : H or L
Input clamp current	I _{IK}	±20	mA	$V_i < 0 \text{ or } V_i > V_{CC}$
Output clamp current	I _{OK}	±20	mA	$V_{o} < 0 \text{ or } V_{o} > V_{cc}$
Continuous output current	Io	±25	mA	$V_{\rm o} = 0$ to $V_{\rm cc}$
$\begin{tabular}{ll} \hline Continuous current through \\ V_{cc} \ or \ GND \\ \hline \end{tabular}$	I _{CC} or I _{GND}	±25	mA	
Maximum power dissipation at Ta = 25°C (in still air) *3	P _T	200	mW	
Storage temperature	Tstg	-65 to 150	°C	

Notes:

- The absolute maximum ratings are values which must not individually be exceeded, and furthermore, no two of which may be realized at the same time.
- 1. The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
- 2. This value is limited to 5.5 V maximum.
- 3. The maximum package power dissipation was caluculated using a junction temperature of 150°C.

Recommended Operating Conditions

Item	Symbol	Min	Max	Unit	Test Conditions
Supply voltage range	V_{cc}	4.5	5.5	V	
Input voltage range	V _I	0	5.5	V	
Output voltage range	Vo	0	V _{cc}	V	
Output current	I _{OL}	_	2	mA	V _{CC} = 4.5 to 5.5 V
	I _{OH}	_	-2	_	$V_{CC} = 4.5 \text{ to } 5.5 \text{ V}$
Input rise / fall time (0.3 V to 2.7 V)	t _r , t _f	0	500	ns	$V_{cc} = 4.5 \text{ to } 5.5 \text{ V}$
Operating temperature	Та	-40	85	°C	

Note: Unused or floating inputs must be held high or low.

Electrical Characteristics

Item	Symbol	\mathbf{V}_{cc}	$T_a = 2$	5°C		$T_a = -40 \text{ to } 85^{\circ}\text{C}$		$T_a = -40 \text{ to } 85^{\circ}\text{C}$ Unit		Test Conditions		
		(V)	Min	Тур	Max	Min	Max	='				
Input voltage	V_{IH}	4.5 to 5.5	2.0	_	_	2.0	_	V				
	V _{IL}	4.5 to 5.5		_	0.8	_	0.8	_				
Output voltage	V _{OH}	4.5	4.4	4.5	_	4.4	_	V	$V_{IN} = V_{IL}$	$I_{OH} = -20 \mu A$		
		4.5	4.18	4.31	_	4.13	_			$I_{OH} = -2 \text{ mA}$		
	V_{OL}	4.5		0.0	0.1	_	0.1	_	$V_{\scriptscriptstyle IN}=V_{\scriptscriptstyle IH}$	$I_{OL} = 20 \mu A$		
		4.5	_	0.17	0.26	_	0.33			$I_{OL} = 2 \text{ mA}$		
Input current	I _{IN}	5.5	_	_	±0.1	_	±1.0	μΑ	$V_{IN} = V_{CC} c$	or GND		
Operating current	I _{cc}	5.5	_	_	1.0	_	10.0	μΑ	$V_{IN} = V_{CC}$	or GND		
Quiescent supply current	I _{CCT}	5.5	_	_	2.0		2.9	mA	One input $V_{IN} = 2.4 \text{ V}$, other input V_{CC} or GND			

Switching Characteristics

Item	Symbol	$T_a = 25^{\circ}$	C		Unit	Test Conditions		
		Min	Тур	Max				
Output rise / fall time	t _{TLH} t _{THL}	_	6	10	ns	Test circuit		
Propagation delay time	t _{PLH}		7.5	12	ns	Test circuit		
	t _{PHL}	_	10	17				

 $(C_L = 15 \text{ pF}, t_r = t_f = 6 \text{ ns}, V_{CC} = 5 \text{ V})$

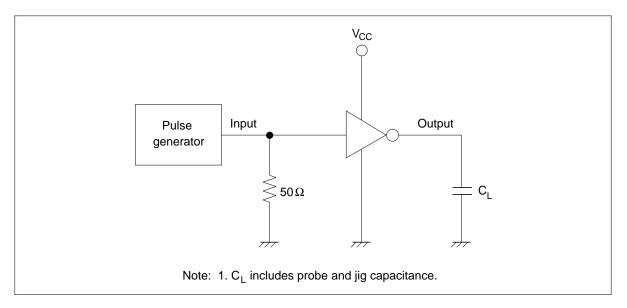
Item	Symbol		$T_a = 25^{\circ}C$		$T_a = -40 \text{ to } 85^{\circ}\text{C}$		Unit	Test Conditions	
		\mathbf{V}_{cc}	Min	Тур	Max	Min	Max	_	
Output rise / fall time	t _{TLH} t _{THL}	4.5	_	14	25	_	31	ns	Test circuit
Propagation delay time	t _{PLH}	4.5	_	11.2	16	_	20	ns	Test circuit
	t _{PHL}	4.5	_	16.4	27	_	31	_	
Input capacitance	C _{IN}	_	_	2.5	5	_	5	pF	
Equivalent capacitance	C _{PD}	_	_	10	_	_	_	pF	

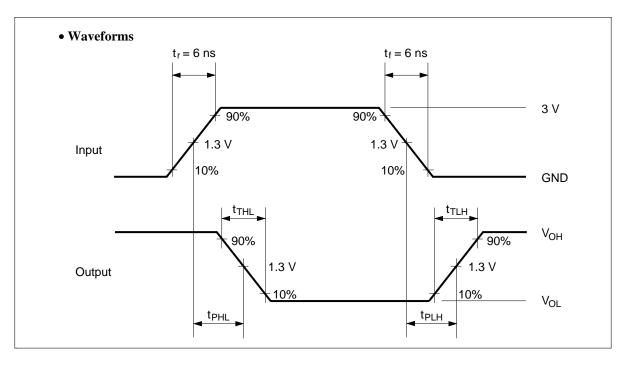
 $(C_L = 50 \text{ pF}, t_r = t_f = 6 \text{ ns})$

Note: C_{PD} is equivalent capacitance inside of the IC calculated from the operating current without load (see test circuit). The average operating current without load is calculated according to the expression below.

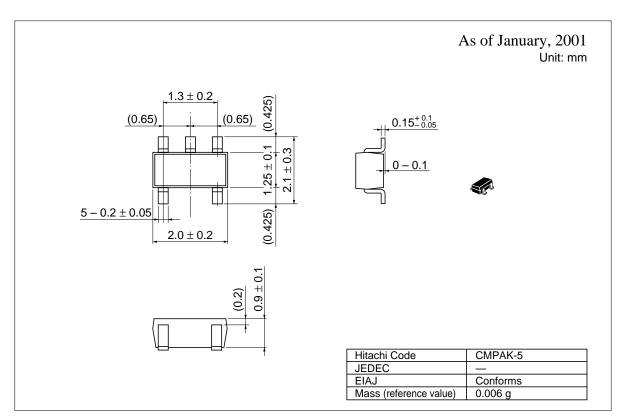
 I_{CC} (opr) = $C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}$

Test Circuit





Package Dimensions



Cautions

- 1. Hitachi neither warrants nor grants licenses of any rights of Hitachi's or any third party's patent, copyright, trademark, or other intellectual property rights for information contained in this document. Hitachi bears no responsibility for problems that may arise with third party's rights, including intellectual property rights, in connection with use of the information contained in this document.
- 2. Products and product specifications may be subject to change without notice. Confirm that you have received the latest product standards or specifications before final design, purchase or use.
- 3. Hitachi makes every attempt to ensure that its products are of high quality and reliability. However, contact Hitachi's sales office before using the product in an application that demands especially high quality and reliability or where its failure or malfunction may directly threaten human life or cause risk of bodily injury, such as aerospace, aeronautics, nuclear power, combustion control, transportation, traffic, safety equipment or medical equipment for life support.
- 4. Design your application so that the product is used within the ranges guaranteed by Hitachi particularly for maximum rating, operating supply voltage range, heat radiation characteristics, installation conditions and other characteristics. Hitachi bears no responsibility for failure or damage when used beyond the guaranteed ranges. Even within the guaranteed ranges, consider normally foreseeable failure rates or failure modes in semiconductor devices and employ systemic measures such as failsafes, so that the equipment incorporating Hitachi product does not cause bodily injury, fire or other consequential damage due to operation of the Hitachi product.
- 5. This product is not designed to be radiation resistant.
- 6. No one is permitted to reproduce or duplicate, in any form, the whole or part of this document without written approval from Hitachi.
- 7. Contact Hitachi's sales office for any questions regarding this document or Hitachi semiconductor products.

HITACH

Hitachi, Ltd.

Semiconductor & Integrated Circuits. Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

URL NorthAmerica http://semiconductor.hitachi.com/

http://www.hitachi-eu.com/hel/ecg Europe http://sicapac.hitachi-asia.com Asia Japan http://www.hitachi.co.jp/Sicd/indx.htm

For further information write to:

Hitachi Semiconductor (America) Inc. 179 East Tasman Drive, Whitebrook Park San Jose,CA 95134

Hitachi Europe Ltd. Electronic Components Group. Lower Cookham Road

Tel: <44> (1628) 585000 Fax: <44> (1628) 585200

Hitachi Europe GmbH Electronic Components Group Dornacher Straße 3 D-85622 Feldkirchen, Munich Germany

Tel: <49> (89) 9 9180-0 Fax: <49> (89) 9 29 30 00

Hitachi Asia Ltd. Hitachi Tower 16 Collyer Quay #20-00, Singapore 049318

URL: http://www.hitachi.com.sg Hitachi Asia Ltd.

(Taipei Branch Office) 4/F, No. 167, Tun Hwa North Road, Hung-Kuo Building,

Taipei (105), Taiwan Tel: <886>-(2)-2718-3666 Fax: <886>-(2)-2718-8180 Telex: 23222 HAS-TP

Hitachi Asia (Hong Kong) Ltd. Group III (Electronic Components) 7/F North Tower World Finance Centre, Harbour City, Canton Road Tsim Sha Tsui, Kowloon,

Hong Kong Tel: <852>-(2)-735-9218 Fax: <852>-(2)-730-0281

URL: http://semiconductor.hitachi.com.hk

Copyright © Hitachi, Ltd., 2001. All rights reserved. Printed in Japan. Colophon 3.0